

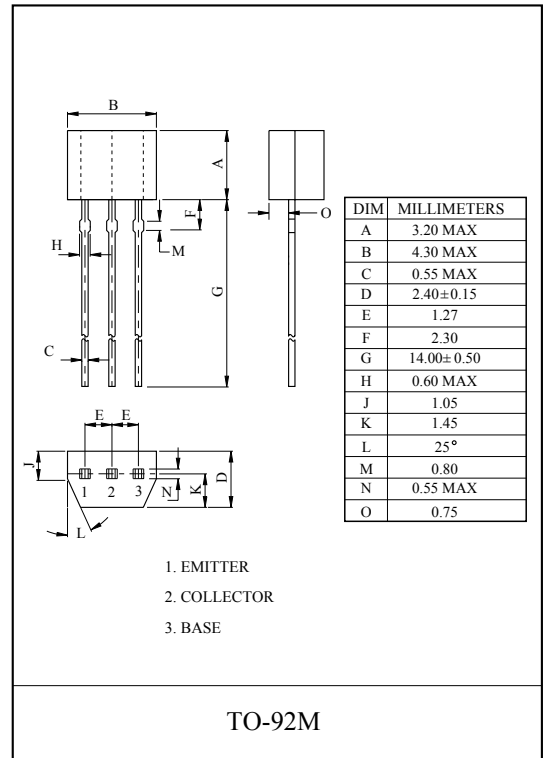
HIGH CURRENT APPLICATION.

FEATURES

- High h_{FE} : $h_{FE}=100 \sim 320$.
- Complementary to KTC3204.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-35	V
Collector-Emitter Voltage	V_{CEO}	-30	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-800	mA
Emitter Current	I_E	800	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=-30V, I_E=0$	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=-5V, I_C=0$	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=-1V, I_C=-100mA$	100	-	320	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-700mA$	35	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA, I_B=-20mA$	-	-	-0.7	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=-1V, I_C=-10mA$	-0.5	-	-0.8	V
Transition Frequency	f_T	$V_{CE}=-5V, I_C=-10mA$	-	120	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	-	19	-	pF

Note : $h_{FE(1)}$ Classification 0:100 ~ 200, Y:160 ~ 320